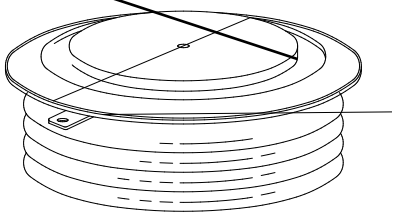
****

T11C



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KP1400/46	4000	4000	4600
KP1400/48	4200	4200	4800
KP1400/50	4400	4400	5000
KP1400/52	4600	4600	5200

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

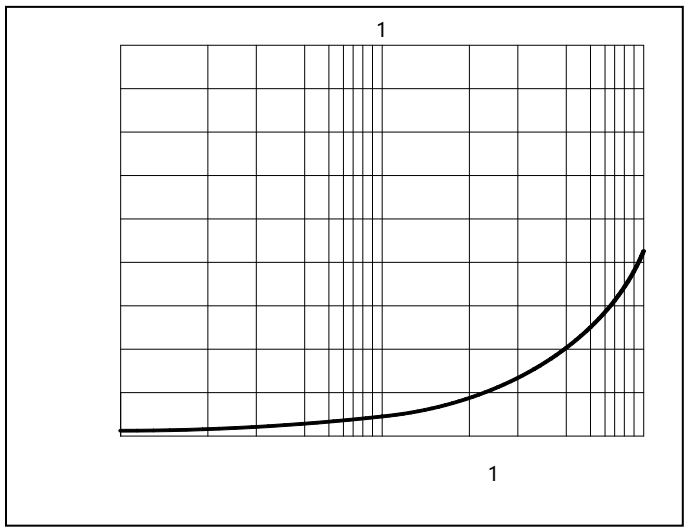
Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 120 mA (3)
Critical rate of voltage rise	dv/dt (4)	2000 V/μ

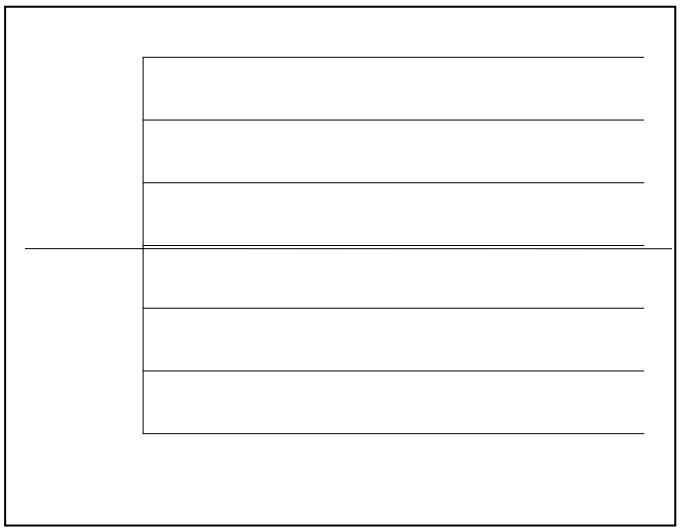
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		200		mA	V_D =12 V;R_L = 3 ohms;T_j = +25 °C
Gate- trigger voltage	V_{GT}	0.7	2.6		V	V_D = 12 V;R_L = 3 ohms;T_j = +25 °C
Peak negative voltage	V_{GRM}		10		V	

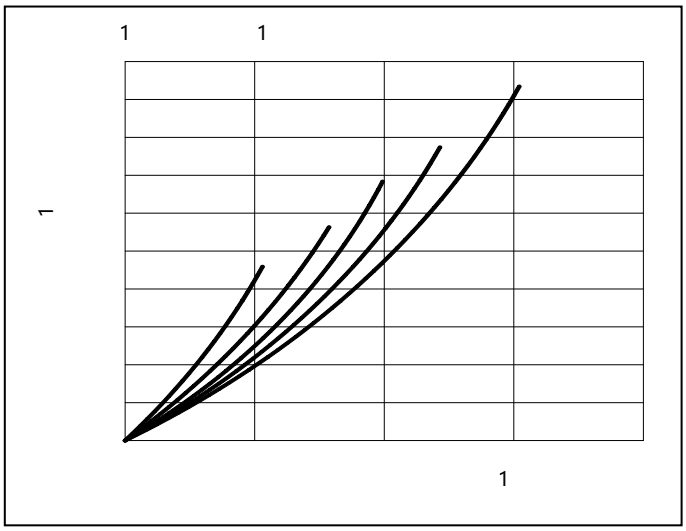
Delay time	t_d			3.0	μs	I_{TM}=100A; V_D=67%V_{DRM} V_G=30V; R_G=10ohms; t_r=0.1μs; t_p=20μs
Turn-off time (with V_R = -5 V)	t_q			600	μs	I_{TM} =2000A; di/dt =-10A/μs; V_R =100V; dv/dt=30V/μs ; V_D= 67%V_{DRM} ;Tj=125
Reverse recovery charge	Q_{rr}		2500		μC	I_{TM}=2000A di/dt=-10A/μs; V_R=100V; T_j=125

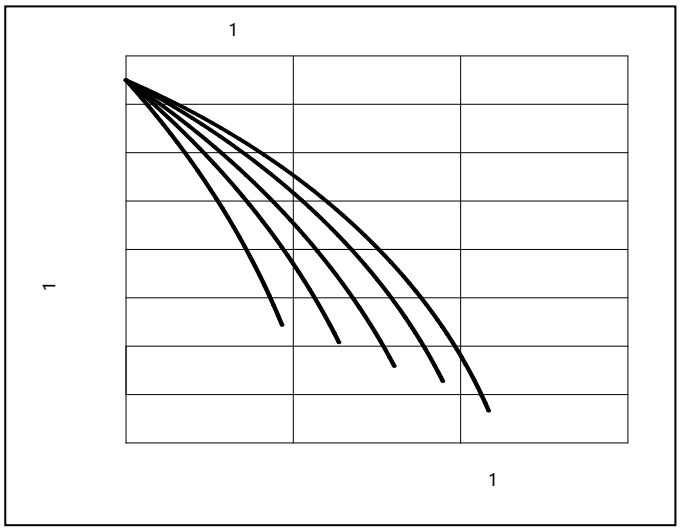
Operating temperature	T_j	-40	+125		°C	
Storage temperature	T_{stg}	-40	+140		°C	
Thermal resistance - junction to case	$R_{\Theta (j-c)}$		0.015		°C/W	Double sided cooled
Thermal resistance - case to heatsink	$R_{\Theta (c-s)}$		0.004		°C/W	Double sided cooled
Mounting force	F	32	36	34	kN	
Weight	m			1.0	kg	

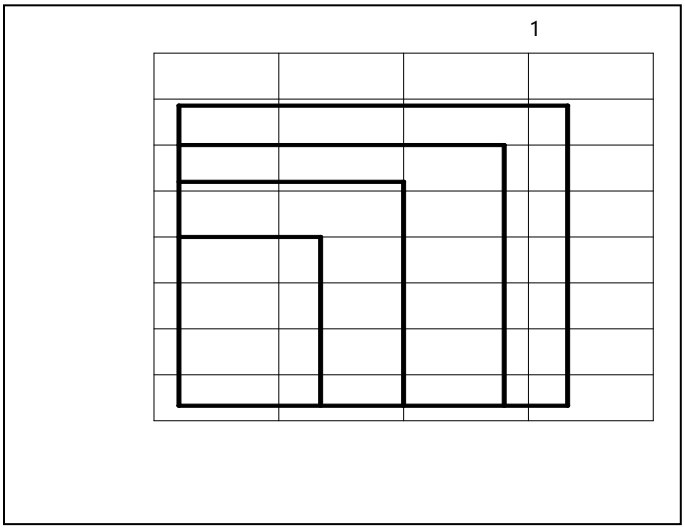
* Mounting surfaces smooth, flat and greased

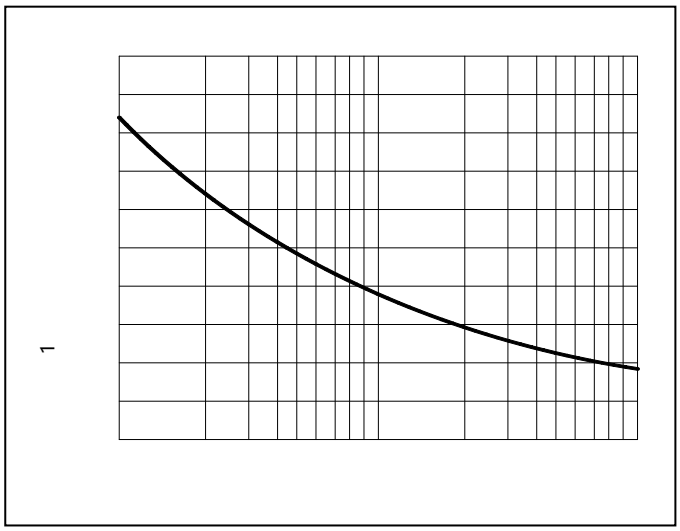

1
1




1
1
1
1


1
1
1


1


1

